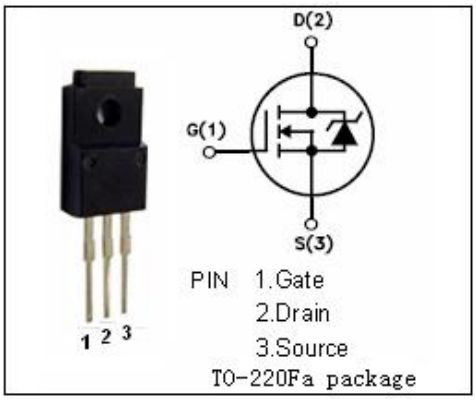
isc N-Channel MOSFET Transistor 2SK1612



DESCRIPTION

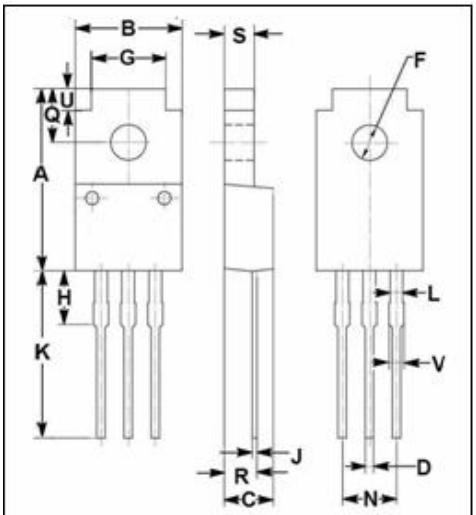
- Drain Current –I_D=3A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}=900V(Min)

APPLICATIONS

- Designed for high voltage, high speed power switching applications such as switching regulators, converters, solenoid and relay drivers.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage (V_{GS}=0)	900	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-continuous@ TC=25℃	3	A
P_{tot}	Total Dissipation@TC=25℃	50	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	16.85	17.15
B	9.90	10.10
C	4.35	4.65
D	0.75	0.80
F	3.20	3.40
G	6.90	7.10
H	5.15	5.45
J	0.45	0.75
K	13.35	13.65
L	1.10	1.30
N	4.98	5.18
Q	4.85	5.15
R	2.95	3.25
S	2.70	2.90
U	1.75	2.05
V	1.30	1.50

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• **ELECTRICAL CHARACTERISTICS (T_C=25℃)**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0; I_D= 1mA	900			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=25V; I_D=1mA	1.0		5.0	V
$R_{DS(on)}$	Drain-Source On-stage Resistance	V_{GS}=10V; I_D=2A		3.8	5.0	Ω
I_{GSS}	Gate Source Leakage Current	V_{GS}= ±30V;V_{DS}= 0			±1	uA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=720V; V_{GS}= 0			100	uA
ton	Turn-on time	V_{GS}=10V;I_D=2A;R_L=100Ω		40		ns
toff	Turn-off time			140		ns